Journal of Crystal Growth 105 (1990) 393–396
North-Holland

AUTHOR INDEX

Abe, T., see Nakajima 105 (1990) 116
Abernathy, C.R., S.J. Pearton, F. Ren, W.S. Hobson, T.R. Fullowan, A. Katz, A.S. Jordan and J. Kovalchick, Carbon doping of III–V compounds grown by MOMBE 105 (1990) 375
Akatsuka, T., see Konagai 105 (1990) 359
Alaoui, F., see Benchimol 105 (1990) 135
Alexandre, F., see Benchimol 105 (1990) 135
Ando, H., A. Sandhu, H. Ishikawa and T. Fujii, GaAs/AlGaAs quantum well structures grown by gas-source MBE using TEG, TEA, and AsH_3 105 (1990) 149
Andrews, D.A., see Murrell 105 (1990) 199
Andrews, D.A., see Skevington 105 (1990) 371
Aoyagi, Y., see Nagata 105 (1990) 52
Aoyagi, Y., see Iimura 105 (1990) 230
Asahi, H., see Kaneko 105 (1990) 69
Asahi, H., see Okuno 105 (1990) 185
Asonen, H., K. Rakennus, K. Tappura, M. Hovinen and M. Pessa, Growth of InP, InGaAs, and InGaAsP on InP by gas-source molecular beam epitaxy 105 (1990) 101

Badoz, P.A., see Le Corre 105 (1990) 234
Baillargeon, J.N., K.Y. Cheng, K.C. Hsieh and C.L. Wei, Growth and silicon doping of $Al_xGa_{1-x}P$ on GaP by gas source molecular beam epitaxy 105 (1990) 106
Baird, R.W., see Fraas 105 (1990) 35
Balk, P., see Kamp 105 (1990) 178
Balk, P., see Musolf 105 (1990) 271
Balk, P., see Weyers 105 (1990) 383
Ballingall, J.M., see Hersee 105 (1990) 282
Baumeister, H., see Veuhoff 105 (1990) 353
Baur, B., see Heinecke 105 (1990) 143
Benchimol, J.L., F. Alaoui, Y. Gao, G. Le Roux, E.V.K. Rao and F. Alexandre, Chemical beam epitaxy of indium phosphide 105 (1990) 135
Bensaoula, A., H. Hansen, H.C. Chen, J.T. Zborowski, K.D. Jamison, A. Ignatiev, H.D. Shih and Y.K. Tao, A RHEED and XPS study of $In_xGa_{1-x}As$ on GaAs grown by chemical beam epitaxy 105 (1990) 227
Brandt, O., see Veuhoff 105 (1990) 353
Briones, F., see Horikoshi 105 (1990) 326
Bulle-Lieuwma, C.W.T., see Thijs 105 (1990) 339

Camarda, R.M., see Yang 105 (1990) 162
Caulet, J., see Le Corre 105 (1990) 234
Chen, H.C., see Bensaoula 105 (1990) 227
Cheng, K.Y., see Baillargeon 105 (1990) 106
Chin, T.P., see Tu 105 (1990) 195
Chin, T.P., see Liang 105 (1990) 240
Chiu, T.H., see Cunningham 105 (1990) 111
Chiu, T.H., J.E. Cunningham, A. Robertson, Jr. and D.L. Malm, Atomic layer epitaxy of GaAs by chemical beam epitaxy 105 (1990) 155
Cunningham, J.E., T.H. Chiu, A. Ourmazd, W. Jan and K.Y. Kuo, Diffusion limited δ-doping profiles in GaAs grown by gas source molecular beam epitaxy 105 (1990) 111
Cunningham, J.E., see Chiu 105 (1990) 155

Dapkus, P.D., see Maa 105 (1990) 213
Davies, G.J., see Murrell 105 (1990) 199
Davies, G.J., see Scott 105 (1990) 249
Davies, G.J., see Skevington 105 (1990) 371
Deppert, K., see Schmidt 105 (1990) 306
Deppert, K., see Paulsson 105 (1990) 312
Duboz, J.Y., see Le Corre 105 (1990) 234

Fairbrother, D.H., see Murrell 105 (1990) 199
Foord, J.S., see Murrell 105 (1990) 199
Foxon, C.T., see Gibson 105 (1990) 81
Foxon, C.T., Understanding growth mechanisms using metalorganic sources 105 (1990) 87
Fraas, L.M., E. Malocsay, V. Sundaram, R.W. Baird, B.Y. Mao and G.Y. Lee, High throughput vacuum chemical epitaxy 105 (1990) 35
Fujii, T., see Ando 105 (1990) 149
Fujii, T., M. Sugawara, S. Yamazaki and K. Nakajima, Macroscopic mechanism of group V interdiffusion in undoped InGaAs/InP quantum wells grown by MOVPE 105 (1990) 348
Fukamachi, T., see Konagai 105 (1990) 359
Fullowan, T.R., see Abernathy 105 (1990) 375

Gao, Y., see Benchimol 105 (1990) 135
Garbinski, P.A., see Yang 105 (1990) 162
Gibson, E.M., C.T. Foxon, J. Zhang and B.A. Joyce, Modulated molecular beam and RHEED studies of MBE and MOMBE growth 105 (1990) 81
Goldstein, L., Optoelectronic devices by GSMBE 105 (1990) 93

Gonda, S., see Kaneko 105 (1990) 69
Gonda, S., see Okuno 105 (1990) 185
Gotoda, M., see Morishita 105 (1990) 221
Guenais, B., see Le Corre 105 (1990) 234
Guivarc'h, A., see Le Corre 105 (1990) 234

Hafich, M.J., see Lee 105 (1990) 244
Hansen, H., see Bensaoula 105 (1990) 227
Hata, M., see Isu 105 (1990) 209
Heinecke, H., B. Baur, R. Höger and A. Miklis, Growth of high purity InP by metalorganic MBE (CBE) 105 (1990) 143
Heinecke, H., see Kamp 105 (1990) 178
Hersee, S.D. and J.M. Ballingall, A gas handling system for MOMBE growth 105 (1990) 282
Hiratani, Y., see Ohki 105 (1990) 77
Hirayama, H., M. Hiroi, K. Koyama and T. Tatsumi, Gas source Si-MBE 105 (1990) 46
Hiroi, M., see Hirayama 105 (1990) 46
Hirose, F., see Suemitsu 105 (1990) 203
Hobson, W.S., see Abernathy 105 (1990) 375
Hofmann, H., see Musolf 105 (1990) 271
Höger, R., see Heinecke 105 (1990) 143
Horikoshi, Y., H. Yamaguchi, F. Briones and M. Kawashima, Growth process of III–V compound semiconductors by migration-enhanced epitaxy 105 (1990) 326
Houng, Y.M., CBE growth of AlGaAs/GaAs heterostructures and their device applications 105 (1990) 124
Houng, Y.M., see Lee 105 (1990) 168
Hovinen, M., see Asonen 105 (1990) 101
Hsieh, K.C., see Baillargeon 105 (1990) 106

Iga, K., see Uchida 105 (1990) 366
Ignatiev, A., see Bensaoula 105 (1990) 227
Iimura, Y., see Nagata 105 (1990) 52
Iimura, Y., K. Nagata, Y. Aoyagi and S. Namba, Surface segregation of indium during growth of InGaAs in chemical beam epitaxy 105 (1990) 230
Imaizumi, M., see Morishita 105 (1990) 221
Ishikawa, H., see Ando 105 (1990) 149
Isu, T., M. Hata and A. Watanabe, Anomalous temperature dependence of growth rate of GaAs grown by trimethylgallium and arsine molecular beams and two competing growth mechanisms 105 (1990) 209
Itoh, H., see Komeno 105 (1990) 30
Iwamura, H., see Naganuma 105 (1990) 254

Jackson, S.L., see McCollum 105 (1990) 316
Jamison, K.D., see Bensaoula 105 (1990) 227
Jan, W., see Cunningham 105 (1990) 111
Jeppesen, S., see Schmidt 105 (1990) 306
Jeppesen, S., see Paulsson 105 (1990) 312
Jönsson, J., see Schmidt 105 (1990) 306
Jönsson, J., see Paulsson 105 (1990) 312
Jordan, A.S., see Abernathy 105 (1990) 375
Joyce, B.A., see Gibson 105 (1990) 81
Joyce, T.B., An integrated safety system for CBE 105 (1990) 299

Kamp, M., M. Weyers, H. Heinecke, H. Lüth and P. Balk, MOMBE of InAs on GaAs 105 (1990) 178
Kaneko, T., Asahi, H., Y. Okuno, T.W. Kang and S. Gonda, Observations on RHEED intensity oscillations during the growth of GaSb and InAs by MOMBE 105 (1990) 69
Kaneko, T., see Okuno 105 (1990) 185
Kang, T.W., see Kaneko 105 (1990) 69
Kang, T.W., see Okuno 105 (1990) 185
Kasai, K., see Komeno 105 (1990) 30
Katz, A., see Abernathy 105 (1990) 375
Kawashima, M., see Horikoshi 105 (1990) 326
Kohl, A., see Weyers 105 (1990) 383
Komeno, J., H. Tanaka, N. Tomesakai, H. Itoh, T. Ohori, M. Takikawa, M. Suzuki and K. Kasai, Recent progress in MOVPE for HEMT LSIs 105 (1990) 30
Konagai, M., T. Yamada, T. Akatsuka, S. Nozaki, R. Miyake, K. Saito, T. Fukamachi, E. Tokumitsu and K. Takahashi, Metallic p-type GaAs and InGaAs grown by MOMBE 105 (1990) 359
Kondo, K., see Maeda 105 (1990) 191
Kovalchick, J., see Abernathy 105 (1990) 375
Koyama, K., see Hirayama 105 (1990) 46
Koyama, F., see Uchida 105 (1990) 366
Kuo, K.Y., see Cunningham 105 (1990) 111

Lambert, M., A. Péralès, R. Vergnaud and C. Starck, High-purity InP grown by gas source molecular beam epitaxy (GSMBE) 105 (1990) 97
Le Corre, A., B. Guenais, A. Guivarc'h, D. Lecrosnier, J. Caulet, M. Minier, G. Ropars, P.A. Badoz and J.Y. Duboz, Epitaxial growth of lattice matched metallic $ErP_{0.6}As_{0.4}$ on (001) and (111) GaAs with a GSMBE system 105 (1990) 234
Le Roux, G., see Benchimol 105 (1990) 135
Lecrosnier, D., see Le Corre 105 (1990) 234
Lee, B.J., Y.M. Houng, J.N. Miller and J.E. Turner, Carbon incorporation in AlGaAs grown by CBE 105 (1990) 168
Lee, G.Y., see Fraas 105 (1990) 35
Lee, H.Y., M.J. Hafich and G.Y. Robinson, The effect of growth pause on the composition of InGaP/GaAs heterointerfaces 105 (1990) 244
Liang, B.W., see Tu 105 (1990) 195
Liang, B.W., T.P. Chin, L.Y. Wang and C.W. Tu, A study of metalorganic molecular beam epitaxy growth of InAs by mass

spectrometry and reflection high-energy electron diffraction 105 (1990) 240
Lüth, H., see Kamp 105 (1990) 178
Lyons, M.H., see Scott 105 (1990) 249

Maa, B.Y. and P.D. Dapkus, Studies of TMGa adsorption on thin GaAs and InAs (001) layers 105 (1990) 213
Maeda, T., J. Saito and K. Kondo, In situ XPS characterization of triethylgallium exposed GaAs and AlAs surfaces 105 (1990) 191
Malm, D.L., see Chiu 105 (1990) 155
Malocsay, E., see Fraas 105 (1990) 35
Mao, B.Y., see Fraas 105 (1990) 35
Martin, T. and C.R. Whitehouse, Modulated-beam mass spectrometry studies of the MOMBE growth of (100) GaAs and $In_{0.1}Ga_{0.9}As$ 105 (1990) 57
Maruno, S., see Morishita 105 (1990) 221
Marx, D., see Weyers 105 (1990) 383
McCollum, M.J., S.L. Jackson, I. Szafranek and G.E. Stillman, Effects of high source flow and high pumping speed on gas source molecular beam epitaxy/chemical beam epitaxy 105 (1990) 316
Mifsud, V.J., P.W. Sullivan and D. Williams, Progress in the design of CBE systems 105 (1990) 289
Miklis, A., see Heinecke 105 (1990) 143
Miller, J.N., see Lee 105 (1990) 168
Minier, M., see Le Corre 105 (1990) 234
Mise, K., see Uchida 105 (1990) 366
Miyake, R., see Konagai 105 (1990) 359
Miyamoto, N., see Suemitsu 105 (1990) 203
Montie, E.A., see Thijs 105 (1990) 339
Morishita, Y., M. Imaizumi, M. Gotoda, S. Maruno, Y. Nomura and H. Ogata, Transient behavior in RHEED intensity oscillations observed in chemical beam epitaxy of InP 105 (1990) 221
Murrell, A.J., A.T.S. Wee, D.H. Fairbrother, N.K. Singh, J.S. Foord, G.J. Davies and D.A. Andrews, Surface studies of the thermal decomposition of triethylgallium on GaAs (100) 105 (1990) 199
Musolf, J., M. Weyers, P. Balk, M. Zimmer and H. Hofmann, Substituted arsines as As sources in MOMBE 105 (1990) 271
Musolf, J., see Weyers 105 (1990) 383

Naganuma, M., M. Notomi, H. Iwamura, M. Okamoto, T. Nishida and T. Tamamura, InGaAs/InP quantum well wires fabricated by GSMBE, MOCVD, and selective chemical etching techniques 105 (1990) 254
Nagata, K., Y. Iimura, Y. Aoyagi and S. Namba, Laser assisted chemical beam epitaxy 105 (1990) 52
Nagata, K., see Iimura 105 (1990) 230
Nakajima, K., see Fujii 105 (1990) 348
Nakajima, M., A. Takamori, T. Yokotsuka, K. Uchiyama and T. Abe, Study of AlInP and GaInP grown by gas source molecular beam epitaxy (GSMBE) 105 (1990) 116
Namba, S., see Nagata 105 (1990) 52
Namba, S., see Iimura 105 (1990) 230
Nishida, T., see Naganuma 105 (1990) 254
Nomura, Y., see Morishita 105 (1990) 221
Notomi, M., see Naganuma 105 (1990) 254
Nozaki, S., see Konagai 105 (1990) 359

Ogata, H., see Morishita 105 (1990) 221
Ohki, Y. and Y. Hiratani, Mass spectrometric study of the reaction of trimethylgallium and GaAs 105 (1990) 77
Ohori, T., see Komeno 105 (1990) 30
Okamoto, M., see Naganuma 105 (1990) 254
Okuno, Y., see Kaneko 105 (1990) 69
Okuno, Y., H. Asahi, T. Kaneko, T.W. Kang and S. Gonda, Surface diffusion lengths of Ga molecules during GaAs MOMBE (metalorganic molecular beam epitaxy) growth 105 (1990) 185
Ourmazd, A., see Cunningham 105 (1990) 111

Paulsson, G., see Schmidt 105 (1990) 306
Paulsson, G., K. Deppert, S. Jeppesen, J. Jönsson, L. Samuelson and P. Schmidt, Reflectance-difference detection of growth oscillations 105 (1990) 312
Pearton, S.J., see Abernathy 105 (1990) 375
Péralès, A., see Lambert 105 (1990) 97
Pessa, M., see Asonen 105 (1990) 101

Rakennus, K., see Asonen 105 (1990) 101
Rao, E.V.K., see Benchimol 105 (1990) 135
Rejman-Greene, M.A.Z., see Scott 105 (1990) 249
Ren, F., see Abernathy 105 (1990) 375
Robertson, Jr., A., see Chiu 105 (1990) 155
Robinson, G.Y., see Lee 105 (1990) 244
Ropars, G., see Le Corre 105 (1990) 234

Saito, J., see Maeda 105 (1990) 191
Saito, K., see Konagai 105 (1990) 359
Samuelson, L., see Schmidt 105 (1990) 306
Samuelson, L., see Paulsson 105 (1990) 312
Sandhu, A., see Ando 105 (1990) 149
Schmidt, P., K. Deppert, S. Jeppesen, J. Jönsson, G. Paulsson and L. Samuelson, A compact VCE growth system for in situ studies of epitaxy 105 (1990) 306
Schmidt, P., see Paulsson 105 (1990) 312
Scott, E.G., M.H. Lyons, M.A.Z. Rejman-Greene and G.J. Davies, The growth of

InP/InGaAs multi-quantum well modulator arrays by gas source MBE 105 (1990) 249
Shih, H.D., see Bensaoula 105 (1990) 227
Singh, N.K., see Murrell 105 (1990) 199
Skevington, P.J., D.A. Andrews and G.J. Davies, Anomalous silicon and tin doping behaviour in indium phosphide grown by chemical beam epitaxy 105 (1990) 371
Speckman, D.M. and J.P. Wendt, Monoethylarsine as a novel replacement for arsine in the vapor deposition of GaAs 105 (1990) 275
Starck, C., see Lambert 105 (1990) 97
Stillman, G.E., see McCollum 105 (1990) 316
Stringfellow, G.B., Alternate sources and growth chemistry for OMVPE and CBE processes 105 (1990) 260
Sudbo, A.S., see Yang 105 (1990) 162
Suemitsu, M., F. Hirose, Y. Takakuwa and N. Miyamoto, Growth kinetics in silane gas-source molecular beam epitaxy 105 (1990) 203
Sugawara, M., see Fujii 105 (1990) 348
Sullivan, P.W., see Mifsud 105 (1990) 289
Sundaram, V., see Fraas 105 (1990) 35
Suzuki, M., see Komeno 105 (1990) 30
Szafranek, I., see McCollum 105 (1990) 316

Takahashi, K., see Konagai 105 (1990) 359
Takakuwa, Y., see Suemitsu 105 (1990) 203
Takamori, A., see Nakajima 105 (1990) 116
Takikawa, M., see Komeno 105 (1990) 30
Tamamura, T., see Naganuma 105 (1990) 254
Tanaka, H., see Komeno 105 (1990) 30
Tao, Y.K., see Bensaoula 105 (1990) 227
Tappura, K., see Asonen 105 (1990) 101
Tatsumi, T., see Hirayama 105 (1990) 46
Thijs, P.J.A., E.A. Montie, T. van Dongen and C.W.T. Bulle-Lieuwma, Improved 1.5 μm wavelength lasers using high quality LP-OMVPE grown strained-layer InGaAs quantum wells 105 (1990) 339
Tokumitsu, E., see Konagai 105 (1990) 359
Tomesakai, N., see Komeno 105 (1990) 30
Treichler, R., see Veuhoff 105 (1990) 353
Tsang, W.T., Progress in chemical beam epitaxy 105 (1990) 1
Tsang, W.T., see Yang 105 (1990) 162
Tu, C.W., B.W. Liang and T.P. Chin, The effects of arsenic overpressure in metal-organic molecular beam epitaxy of GaAs and InAs 105 (1990) 195
Tu, C.W., see Liang 105 (1990) 240
Turner, J.E., see Lee 105 (1990) 168

Uchida, T., see Uchida 105 (1990) 366
Uchida, T.K., T. Uchida, K. Mise, F. Koyama and K. Iga, Extremely high Be doped $Ga_{0.47}In_{0.53}As$ growth by chemical beam epitaxy 105 (1990) 366
Uchiyama, K., see Nakajima 105 (1990) 116

Van Dongen, T., see Thijs 105 (1990) 339
Vergnaud, R., see Lambert 105 (1990) 97
Veuhoff, E., H. Baumeister, O. Brandt and R. Treichler, Mg incorporation process during LP-MOVPE of InP, GaInAs and GaInAsP 105 (1990) 353

Wang, L.Y., see Liang 105 (1990) 240
Watanabe, A., see Isu 105 (1990) 209
Wee, A.T.S., see Murrell 105 (1990) 199
Wei, C.L., see Baillargeon 105 (1990) 106
Wendt, J.P., see Speckman 105 (1990) 275
Weyers, M., see Kamp 105 (1990) 178
Weyers, M., see Musolf 105 (1990) 271
Weyers, M., J. Musolf, D. Marx, A. Kohl and P. Balk, Gaseous dopant sources in MOMBE/CBE 105 (1990) 383
Whitehouse, C.R., see Martin 105 (1990) 57
Williams, D., see Mifsud 105 (1990) 289

Yamada, T., see Konagai 105 (1990) 359
Yamaguchi, H., see Horikoshi 105 (1990) 326
Yamazaki, S., see Fujii 105 (1990) 348
Yang, L., A.S. Sudbo, W.T. Tsang, P.A. Garbinski and R.M. Camarda, Monolithically integrated InGaAs/InP MSM–FET photo-receiver prepared by chemical beam epitaxy 105 (1990) 162
Yokotsuka, T., see Nakajima 105 (1990) 116

Zborowski, J.T., see Bensaoula 105 (1990) 227
Zhang, J., see Gibson 105 (1990) 81
Zimmer, M., see Musolf 105 (1990) 271

Journal of Crystal Growth 105 (1990) 397–398
North-Holland

SUBJECT INDEX

Adsorption, 52, 81, 87, 155, 191, 195, 199, 213, 227, 230, 240
Aluminum
– arsenide 191, 282
– gallium arsenide 30, 35, 124, 149, 168, 282, 326, 375
– gallium phosphide 106
– indium phosphide 116
– organic 30, 35, 57, 124, 149, 168, 260, 289, 316
Antimony
– organic 260
Apparatus
– for thin film growth
– – by chemical beam epitaxy
– – – of aluminum gallium arsenide 124
– – – of gallium arsenide 35, 306, 316
– – – of III–V compounds 289, 299
– – by metalorganic molecular beam epitaxy
– – – of gallium arsenide 209
– – – of indium arsenide 240
– – – of III–V compounds 282
– – by molecular beam epitaxy
– – – of gallium arsenide 77, 316
– – – of silicon 46, 203
– – by vapor phase epitaxy
– – – through metalorganic chemical vapor deposition
– – – – of gallium arsenide 275
– for miscellaneous purposes
– – gas cell handling system 289
– – modulated beam mass spectrometry 57
– – reflection difference detection 312
– – safety system for chemical beam epitaxy 299
Arsenic
Organic 260, 271, 275, 289, 383

Beryllium
– organic 383

Characterization methods
– by electrical methods 30, 35, 46, 93, 97, 106, 111, 116, 124, 135, 143, 162, 168, 178, 234, 249, 275, 306, 316, 353, 359, 366, 371, 383
– by electron microscopy 46, 69, 93, 116, 213, 234, 339, 375
– by light scattering 326
– by mass spectrometry 57, 77, 168, 240, 306
– by optical microscopy 101, 106, 116, 366, 375
– by optical properties 116
– by photoluminescence 97, 101, 116, 124, 135, 143, 149, 271, 275, 306, 316, 339, 348, 353, 359
– by reflection high energy electron diffraction 52, 69, 77, 81, 106, 155, 185, 209, 213, 221, 227, 230, 240, 244, 282, 306, 326
– by Rutherford back scattering 178
– by secondary ion mass spectrometry 135, 178, 275, 353, 359, 371, 375
– by X-ray photoelectron spectroscopy 191, 199, 213, 227
– by X-ray methods 101, 116, 124, 135, 234, 244, 249, 366, 375
Computer simulation 359

Devices 1, 30, 35, 93, 124, 162, 234, 249, 282, 339, 359, 375
Diffusional control 111, 185, 348, 375
Dopants 46, 106, 111, 116, 135, 227, 353, 359, 366, 371, 375, 383

Erbium
– phosphide arsenide 234
Etching
– chemical 69, 254

Gallium
– antimonide 69
– arsenide 35, 52, 57, 77, 81, 87, 111, 149, 155, 185, 191, 195, 199, 209, 213, 260, 271, 275, 282, 299, 306, 312, 326, 359, 375, 383
– indium arsenide phosphide 93, 289
– indium phosphide 116
– organic 30, 35, 54, 57, 69, 77, 81, 124, 149, 155, 168, 185, 191, 195, 199, 209, 213, 230, 260, 289, 299, 306, 312, 316, 375, 383
– phosphide 260

Heterojunction 57, 124, 149, 230, 244, 249, 282, 348, 375

Impurity 57, 111, 124, 135, 155, 168, 178, 383
Indium
– arsenide 69, 178, 195, 213, 240
– gallium arsenide 57, 101, 162, 227, 230, 249, 254, 339, 348, 353, 359, 366, 375
– gallium arsenide phosphide 101, 339, 353
– gallium phosphide 244
– organic 57, 69, 135, 143, 178, 230, 260, 289, 316
– phosphide 93, 97, 101, 135, 143, 221, 249, 254, 339, 348, 353, 371, 383
Interface 230, 234, 244, 249, 282, 348, 375

Kinetics
– of growth 35, 52, 57, 69, 77, 81, 87, 111, 135, 143, 178, 185, 191, 195, 199, 203, 209, 213, 227, 230, 240, 260, 271, 275, 282, 312, 366
Lattice mismatch 178, 234, 359

Magnesium
– organic 383
Morphology of growth 306, 375

Perfection of crystals 178, 185, 234

Quantum wells/size effects 93, 149, 244, 249, 254, 282, 339, 348

Safety instrumentation 299
Silicon 46, 203
Solar cells 35
Strain 339
Superlattices 244, 289
Surface processes 46, 149, 191, 326
Surface structure 52, 213, 312

Tellurium
– organic 383
Thin film growth
– by atomic layer epitaxy
– – of gallium arsenide 213
– – of indium arsenide 213
– by chemical beam epitaxy
– – of aluminum gallium arsenide 124, 168
– – of gallium arsenide 35, 52, 155, 260, 306, 312, 316
– – of gallium phosphide 260
– – of indium gallium arsenide 162, 227, 230, 366
– – of indium phosphide 135, 221, 371
– – mechanism of 87
– – progress of 1, 289
– by metalorganic molecular beam epitaxy
– – of aluminum gallium arsenide 149, 375
– – of gallium arsenide 57, 77, 81, 149, 185, 195, 199, 209, 271, 299, 359, 375, 383
– – of indium arsenide 178, 195, 240
– – of indium gallium arsenide 57, 359, 375
– – of indium phosphide 143, 383
– – of III–V compounds 282
– – mechanism of 87
– by molecular beam epitaxy
– – of aluminum arsenide 191
– – of aluminum gallium phosphide 106
– – of aluminum indium phosphide 116
– – of erbium phosphide arsenide 234
– – of gallium arsenide 81, 111, 191, 316
– – of gallium indium arsenide phosphide 93, 249, 254
– – of gallium indium phosphide 116, 244
– – of indium phosphide 93, 97, 249, 254
– – of silicon 203
– – of III–V compounds 326
– by molecular layer epitaxy
– – of silicon 46
– by vapor phase epitaxy
– – through metalorganic chemical vapor deposition
– – – of aluminum gallium arsenide 30
– – – of gallium arsenide 260, 275
– – – of gallium phosphide 260
– – – of indium gallium arsenide 254, 339, 348, 353
– – – of indium gallium arsenide phosphide 339, 353
– – – of indium phosphide 254, 339, 348, 353
Three-five (III–V) compounds 282, 326

Uniformity of growth 30, 35